



## JCT1285SJ 85A SCRs

Rev.1.1

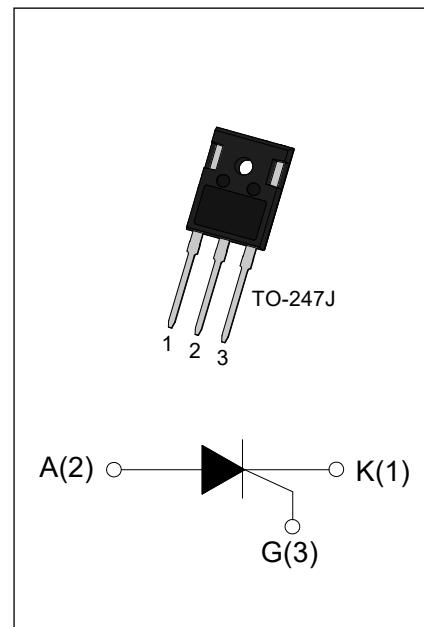
**DESCRIPTION:**

With high ability to withstand the shock loading of large current, JCT1285SJ SCRs provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, UPS,T-tools etc.

Package TO-247J is RoHS compliant. (2011/65/EU)

**MAIN FEATURES**

Symbol	Value	Unit
$V_{DRM} / V_{RRM}$	1200	V
$I_{T(RMS)}$	85	A
$I_{GT}$	10~80	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40~150	°C
Operating junction temperature range	$T_j$	-40~150	°C
Operating temperature range	$T_{op}$	-40~125	°C
Repetitive peak off-state voltage( $T_j=25^{\circ}\text{C}$ )	$V_{DRM}$	1200	V
Repetitive peak reverse voltage( $T_j=25^{\circ}\text{C}$ )	$V_{RRM}$	1200	V
Average on-state current	$I_{T(AV)}$	55	A
RMS on-state current <small>(<math>T_c \leq 105^{\circ}\text{C}</math>)</small>	TO-247J $I_{T(RMS)}$	85	A
Non repetitive surge peak on-state current ( $t_p=10\text{ms}$ )	$I_{TSM}$	1000	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )	$I^2t$	5000	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	$dI/dt$	200	$\text{A}/\mu\text{s}$
Peak gate current	$I_{GM}$	10	A
Average gate power dissipation	$P_{G(AV)}$	1	W

Peak gate power	$P_{GM}$	20	W
Peak pulse voltage ( $T_j=25^\circ C$ ; non-repetitive, off-state; FIG.7)	$V_{PP}$	1.0	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ C$  unless otherwise specified)

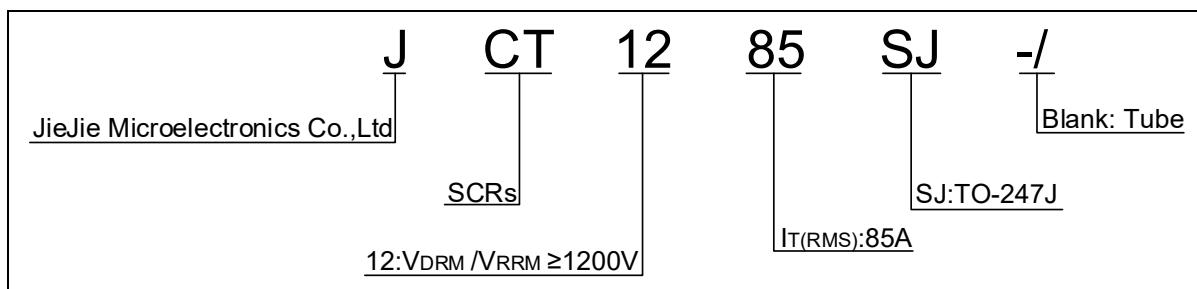
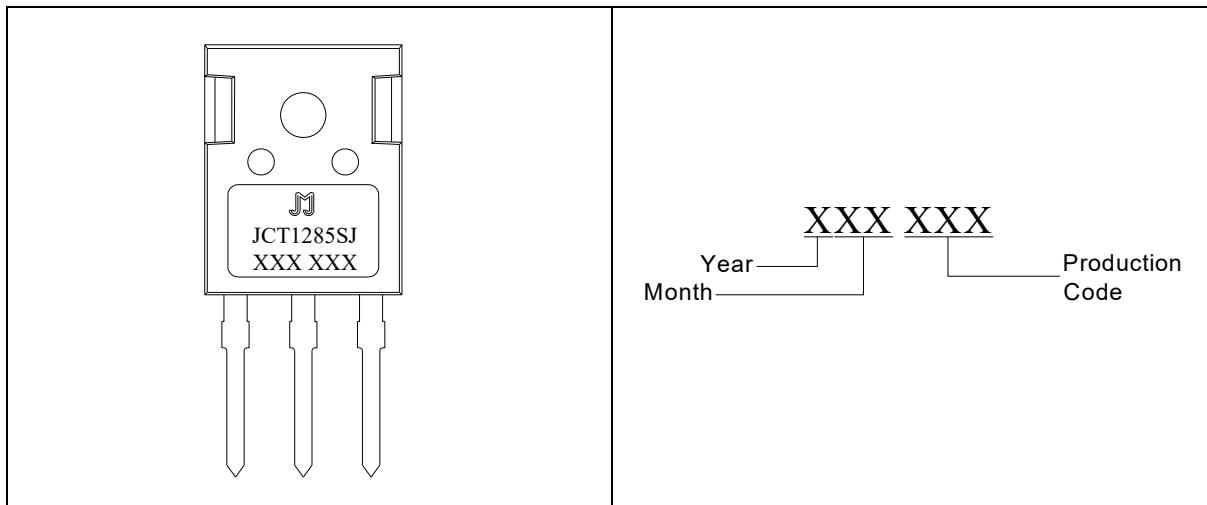
Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V$ $R_L=33\Omega$	10	-	80	mA
$V_{GT}$		-	-	1.2	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=150^\circ C$ $R_L=3.3K\Omega$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	300	mA
$I_H$	$I_T=500mA$	-	-	200	mA
$dv/dt$	$V_D=2/3V_{DRM}$ Gate Open $T_j=150^\circ C$	1500	-	-	V/ $\mu$ s

**STATIC CHARACTERISTICS**

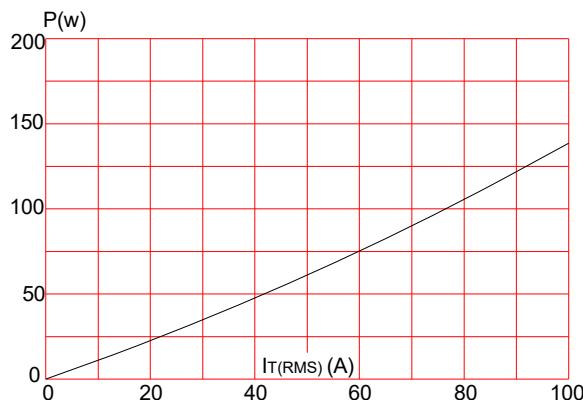
Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=120A$	$tp=380\mu s$	$T_j=25^\circ C$	1.5
$V_{TO}$	Threshold voltage		$T_j=150^\circ C$	1
$R_D$	Dynamic resistance		$T_j=150^\circ C$	5
$I_{DRM}$	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ C$	10
$I_{RRM}$			$T_j=150^\circ C$	5

**THERMAL RESISTANCES**

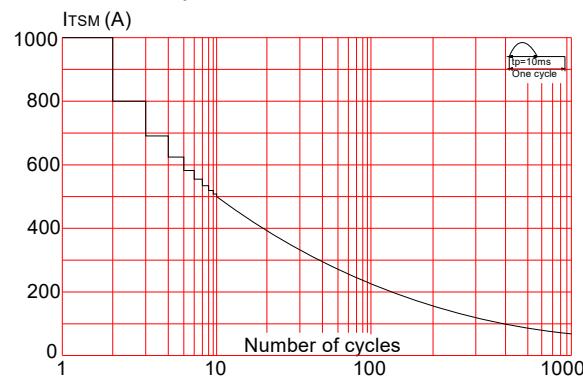
Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case (AC)	TO-247J	0.4	°C/W

**ORDERING INFORMATION****MARKING**

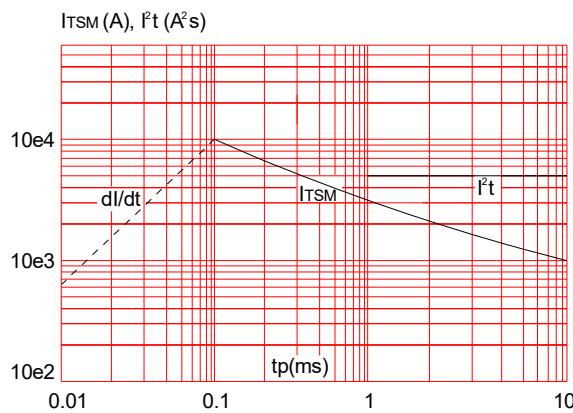
**FIG.1:** Maximum power dissipation versus RMS on-state current



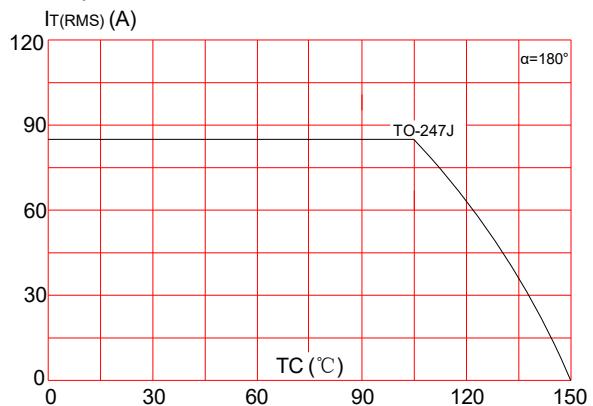
**FIG.3:** Surge peak on-state current versus number of cycles



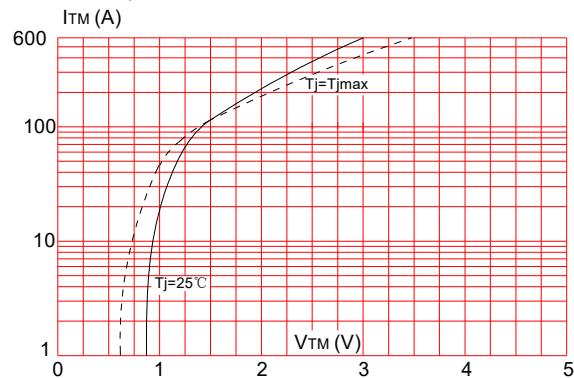
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $\int I^2 t$  ( $dI/dt < 200\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

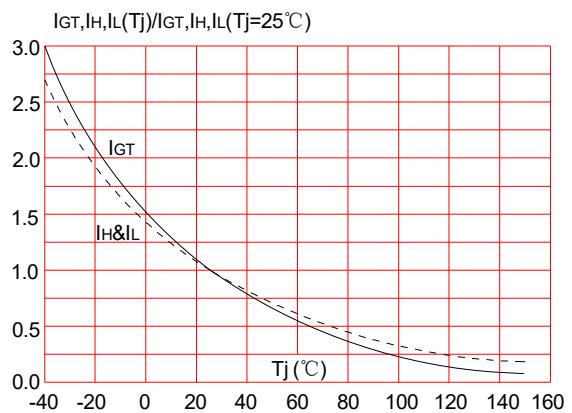
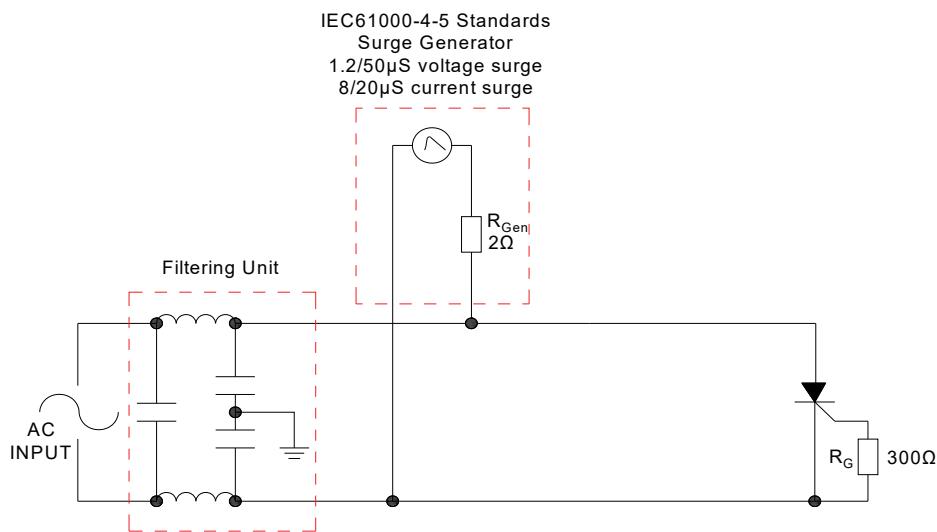


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



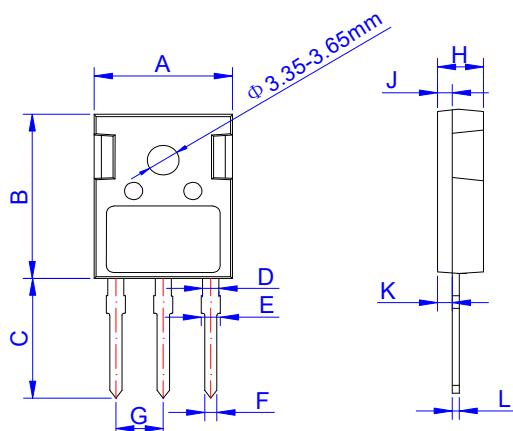
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT1285SJ	1200	10~80	TO-247J	30	Tube

## Document Revision History

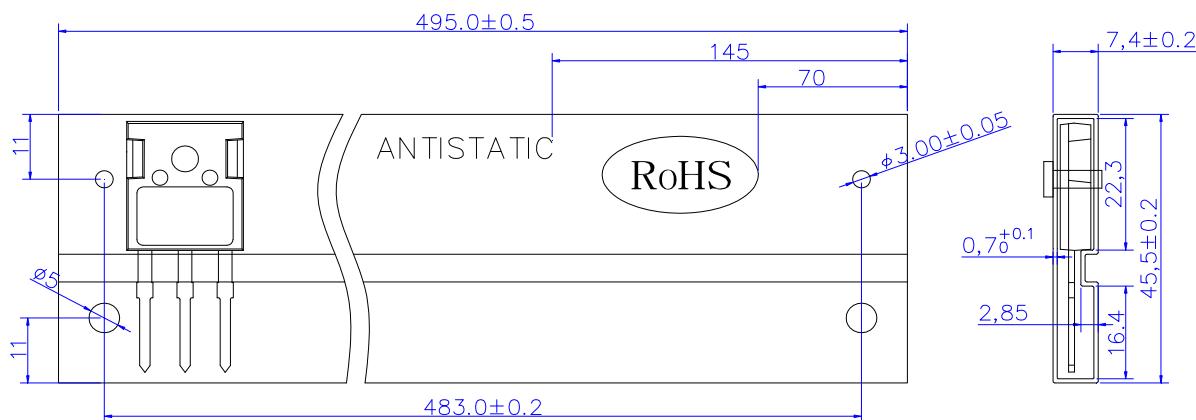
Date	Revision	Changes
Mar 8, 2022	1.1	Last update

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	22.20	0.819	0.827	0.835
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.25		5.65	0.207		0.222
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-247J	TUBE	30	450	2,250



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